

TECHNICAL DATA
DATA SHEET D0122 REV. –

SILICON SCHOTTKY RECTIFIER DIE

Ultra Low Reverse Leakage

200°C Operating Temperature

Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging
- Out Performs 150 Volt Ultrafast Rectifiers

Maximum Ratings:

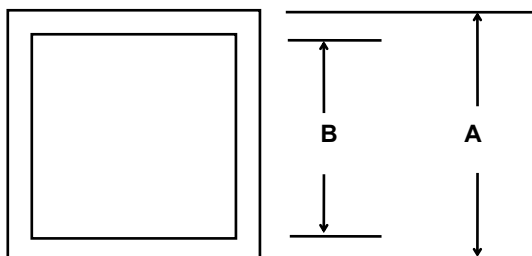
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	60	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, Sine pulse ⁽¹⁾	860	A
Junction Temperature	T_J	-	-55 to +200	°C
Storage Temperature	T_{stg}	-	-55 to +200	°C

Electrical Characteristics:

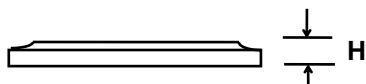
Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V_{F1}	@ 60 A, Pulse, $T_J = 25\text{ °C}$	0.92	V
	V_{F2}	@ 60 A, Pulse, $T_J = 125\text{ °C}$	0.79	V
Reverse Current	I_{R1}	@ $V_R = 150\text{V}$, Pulse, $T_J = 25\text{ °C}$	1.5	mA
	I_{R2}	@ $V_R = 150\text{V}$, Pulse, $T_J = 125\text{ °C}$	24	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ °C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV (p-p)}$	1500	pF

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Mechanical Dimensions: In Inches (mm)



Bottom side metalization Ag-5kA minimum
Top side metalization Al -25kA minimum
Bottom side is cathode, top side is anode
Dimension H =0.0105±0.001(0.27±0.026) (It can be customized according to customer requirements)



A	B
0.200 ± 0.003(5.08 ± 0.08)	0.192 ± 0.003(4.88 ± 0.08)

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